Course guides
230658 - IMT - Introduction to Microelectronic Technologies

Unit in charge: Barcelona School of Telecommunications Engineering
Teaching unit: 710 - EEL - Department of Electronic Engineering.

Degree:
- MASTER'S DEGREE IN ELECTRONIC ENGINEERING (Syllabus 2013). (Optional subject).
- MASTER'S DEGREE IN TELECOMMUNICATIONS ENGINEERING (Syllabus 2013). (Optional subject).
- MASTER'S DEGREE IN ADVANCED TELECOMMUNICATION TECHNOLOGIES (Syllabus 2019). (Optional subject).

Academic year: 2020  ECTS Credits: 5.0  Languages: English

LECTURER

Coordinating lecturer: I. MARTIN

Others:

DEGREE COMPETENCES TO WHICH THE SUBJECT CONTRIBUTES

Transversal:
1. EFFECTIVE USE OF INFORMATION RESOURCES: Managing the acquisition, structuring, analysis and display of data and information in the chosen area of specialisation and critically assessing the results obtained.

2. FOREIGN LANGUAGE: Achieving a level of spoken and written proficiency in a foreign language, preferably English, that meets the needs of the profession and the labour market.

TEACHING METHODOLOGY

- Lectures
- Application classes
- Problem deliveries
- Exams with short questions and problems
- Short oral presentations

LEARNING OBJECTIVES OF THE SUBJECT

Learning objectives of the subject:

The aim of this course is to teach students at an introductory level about the physical principles of semiconductor devices and offer them an overview about the reasons why semiconductor devices are the basis of the electronics industry.

In particular we go in depth in the physical foundations, then we will present in detail diodes and bipolar transistors. Additionally, a brief description and analysis of fundamental properties of basic electron devices will be done.

Learning results of the subject:

- Ability to analyse and predict the general behaviour of semiconductor devices.
- Ability to quantify the electrical properties.
- Ability to obtain the different electrical models to be applied in circuit analysis and design.
STUDY LOAD

<table>
<thead>
<tr>
<th>Type</th>
<th>Hours</th>
<th>Percentage</th>
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<tbody>
<tr>
<td>Self study</td>
<td>86.0</td>
<td>68.80</td>
</tr>
<tr>
<td>Hours large group</td>
<td>39.0</td>
<td>31.20</td>
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</tbody>
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Total learning time: 125 h

CONTENTS

1. Fundamentals

Description:
- Crystal structure
- Atomic structure and wave properties
- Energy bands
- Carrier concentrations
- Currents in semiconductors
- The continuity equation

Full-or-part-time: 42h
Theory classes: 17h 30m
Self study: 24h 30m

2. P/N junctions

Description:
- Band diagram in thermal equilibrium
- Electrostatics
- Steady state I-V characteristics
- Small signal model
- Junction breakdown

Full-or-part-time: 22h
Theory classes: 7h 30m
Self study: 14h 30m

3. Bipolar junction transistor.

Description:
- The transistor effect
- Band diagram
- Common-base I-V characteristics
- Ebers-Moll model
- Small signal model
- Non idealities

Full-or-part-time: 23h
Theory classes: 8h
Self study: 15h
4. Other electron devices

Description:
- Description and analysis of basic optoelectronic devices like photoconductors, photodiodes, solar cells, LED's, lasers, TFT, etc.

Full-or-part-time: 6h
Theory classes: 2h
Self study : 4h

ACTIVITIES

SHORT ANSWER TEST (CONTROL)

Description:
Mid term control.

EXTENDED ANSWER TEST (FINAL EXAMINATION)

Description:
Final examination.

GRADING SYSTEM

Final examination: 45%
Partial examinations and controls: 45%
Oral presentation: 10%

BIBLIOGRAPHY

Basic: